

IRFH5053PbF

Applications

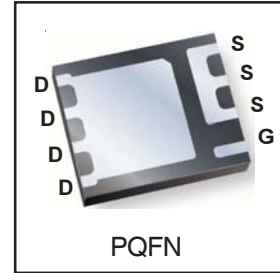
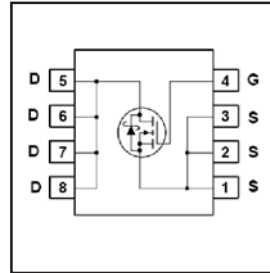
- 3 Phase Boost Converter Applications
- Secondary Side Synchronous Rectification

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ max	Qg
100V	18m Ω @ $V_{GS} = 10V$	24nC

Benefits

- Very low $R_{DS(ON)}$ at 10V V_{GS}
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- 100% Tested for R_G
- Lead-Free (Qualified up to 260°C Reflow)
- RoHS compliant (Halogen Free)
- Low Thermal Resistance
- Large Source Lead for more reliable Soldering



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	9.3	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, V_{GS} @ 10V	7.4	
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	46	
I_{DM}	Pulsed Drain Current ①	75	
P_D @ $T_A = 25^\circ C$	Power Dissipation ⑤	3.1	W
P_D @ $T_A = 70^\circ C$	Power Dissipation ⑤	2.0	
	Linear Derating Factor ⑤	0.025	W/ $^\circ C$
T_J	Operating Junction and	-55 to + 150	$^\circ C$
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	1.6	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	40	

Notes ① through ⑤ are on page 9

IRFH5053PbF

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

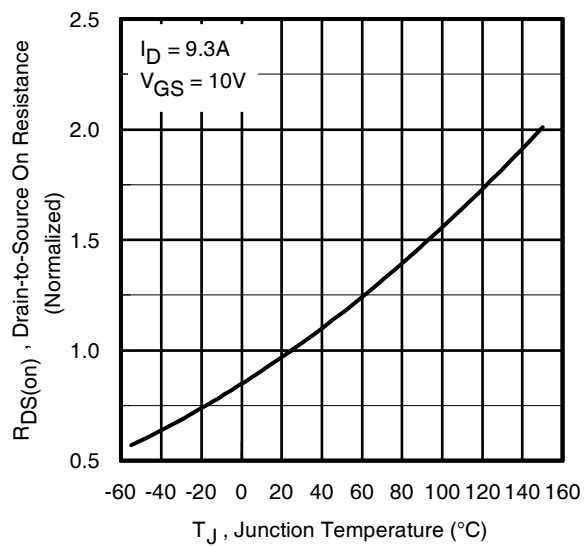
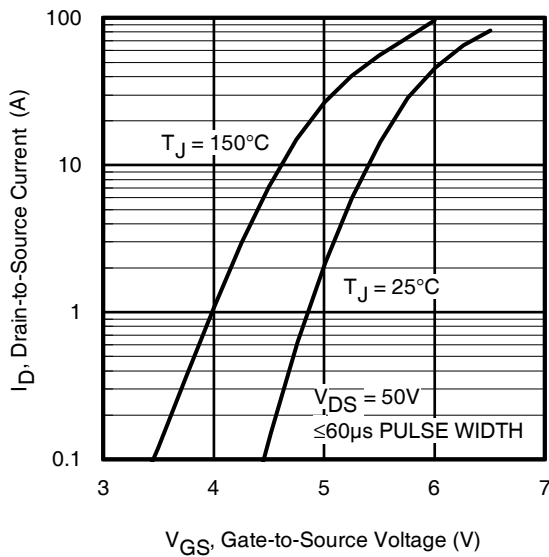
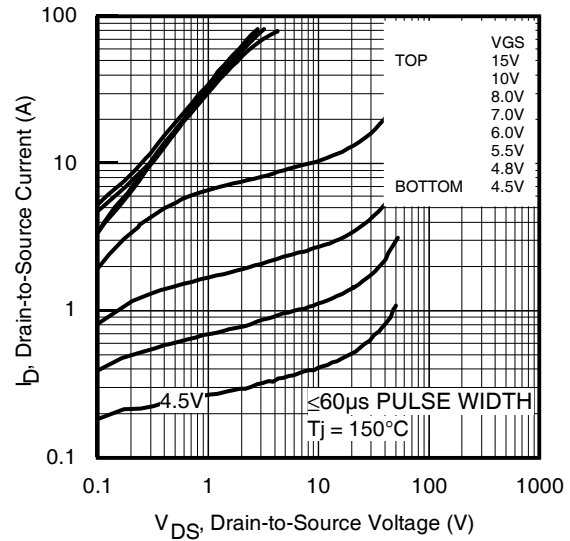
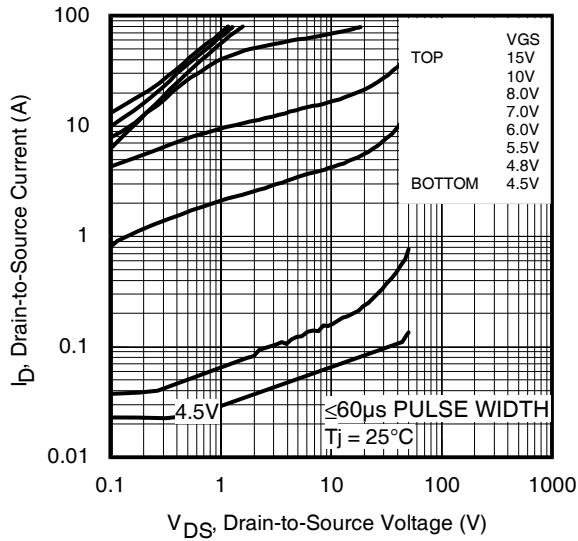
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	14.4	18	$m\Omega$	$V_{GS} = 10V, I_D = 9.3A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	3.7	4.9	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-11	—	$mV/^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 80V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	19	—	—	S	$V_{DS} = 50V, I_D = 7.4A$
Q_g	Total Gate Charge	—	24	36	nC	$V_{DS} = 50V$ $V_{GS} = 10V$ $I_D = 7.4A$ See Fig.17 & 18
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	5.2	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	1.5	—		
Q_{gd}	Gate-to-Drain Charge	—	8.6	—		
Q_{godr}	Gate Charge Overdrive	—	8.7	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	10.1	—		
Q_{oss}	Output Charge	—	12	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
R_G	Gate Resistance	—	0.8	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 50V, V_{GS} = 10V$ $I_D = 7.4A$ $R_G = 1.8\Omega$ See Fig.15
t_r	Rise Time	—	7.5	—		
$t_{d(off)}$	Turn-Off Delay Time	—	18	—		
t_f	Fall Time	—	4.1	—		
C_{iss}	Input Capacitance	—	1510	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	230	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	59	—		$f = 1.0\text{MHz}$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	21	mJ
I_{AR}	Avalanche Current ①	—	7.4	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.8	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	75		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 7.4A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	31	47	ns	$T_J = 25^\circ\text{C}, I_F = 7.4A, V_{DD} = 50V$
Q_{rr}	Reverse Recovery Charge	—	210	320	nC	$di/dt = 800A/\mu s$ ③ See Fig.16
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



IRFH5053PbF

International
IR Rectifier

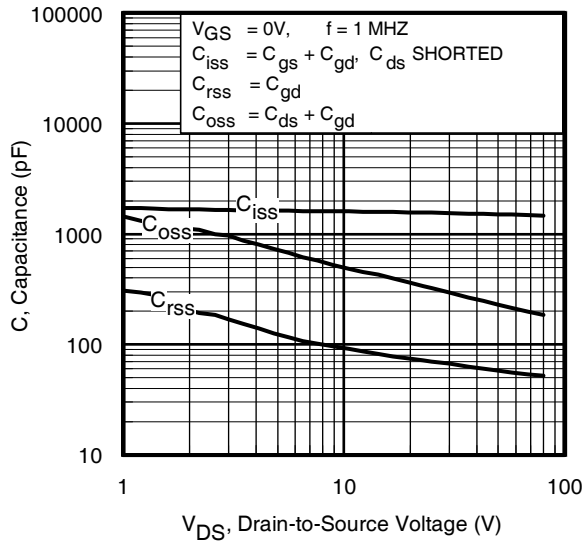


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

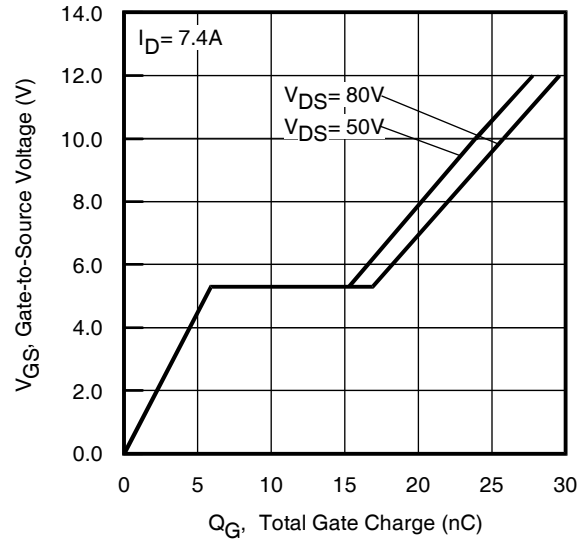


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

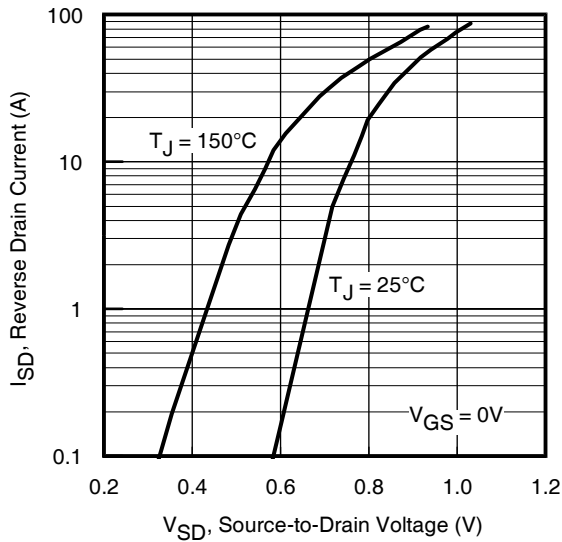


Fig 7. Typical Source-Drain Diode Forward Voltage

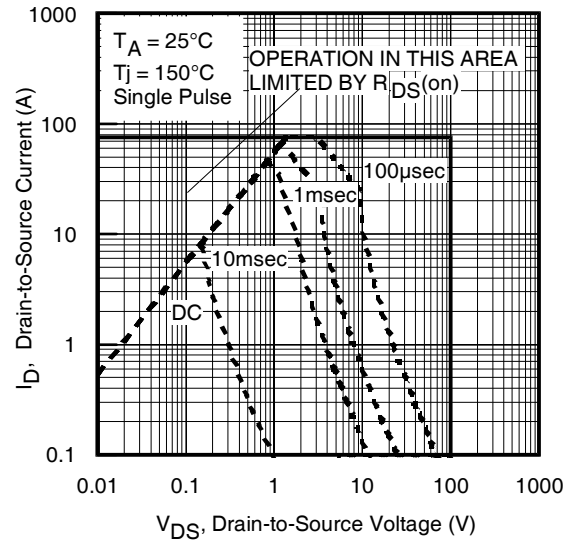


Fig 8. Maximum Safe Operating Area

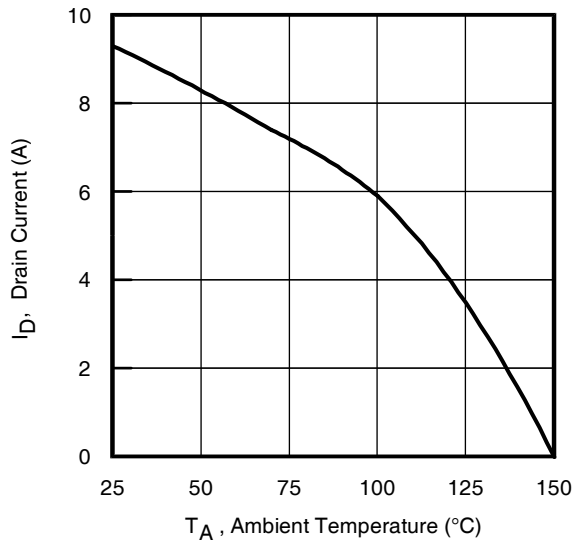


Fig 9. Maximum Drain Current vs. Ambient Temperature

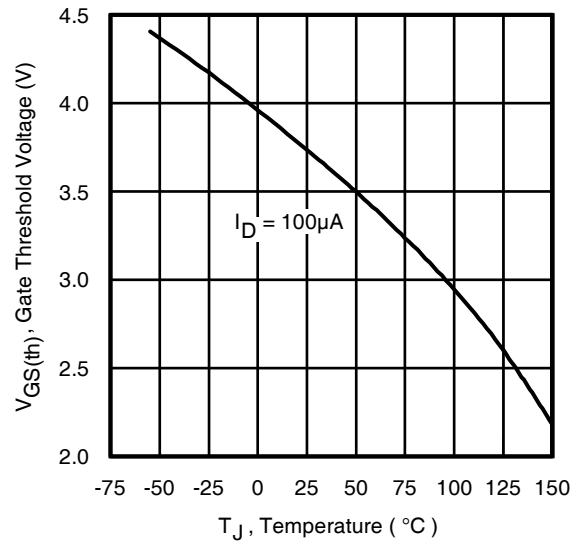


Fig 10. Threshold Voltage vs. Temperature

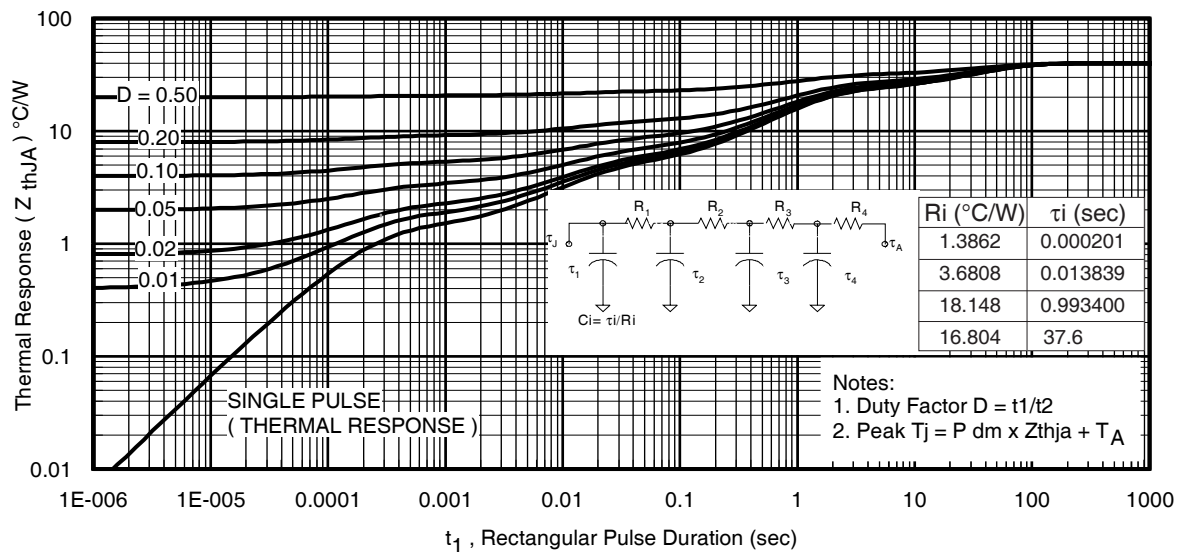


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

IRFH5053PbF

International
IR Rectifier

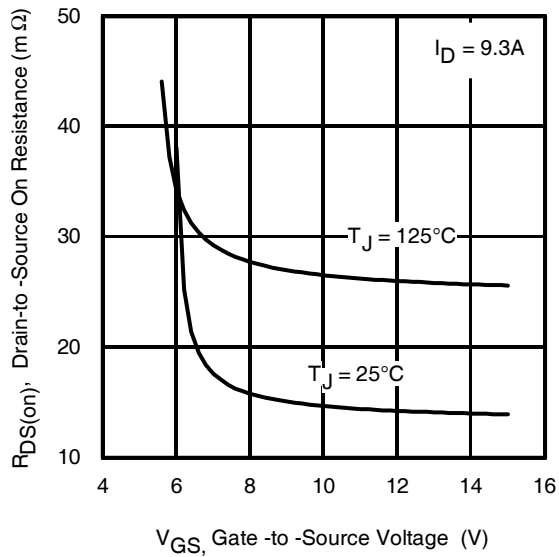


Fig 12. On-Resistance vs. Gate Voltage

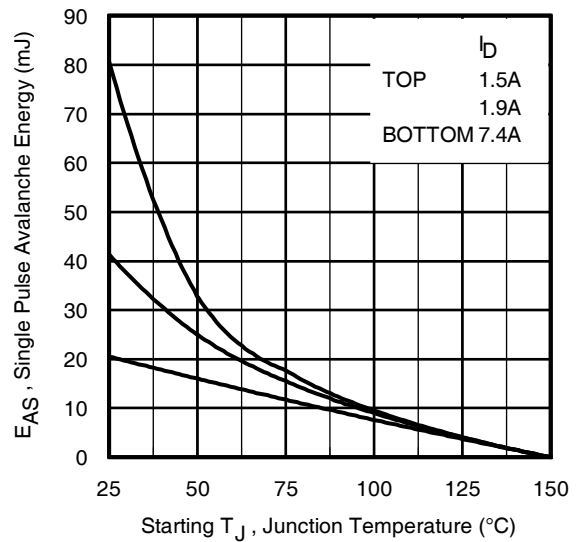


Fig 13. Maximum Avalanche Energy vs. Drain Current

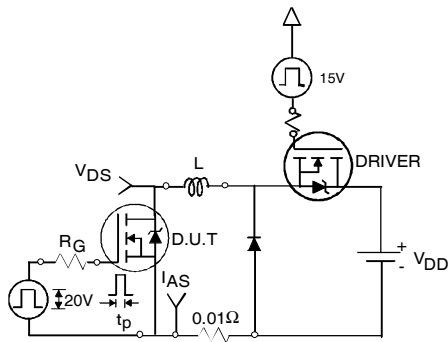


Fig 14a. Unclamped Inductive Test Circuit

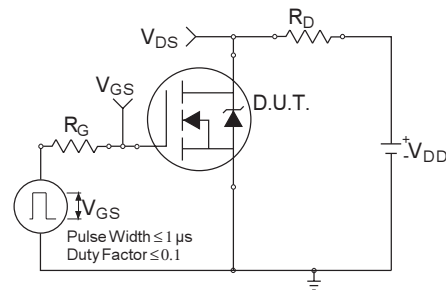


Fig 15a. Switching Time Test Circuit

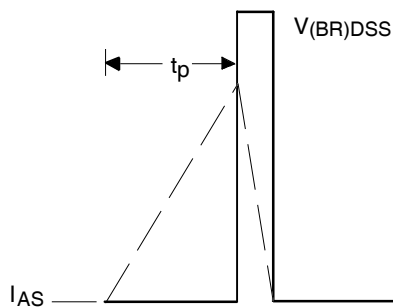


Fig 14b. Unclamped Inductive Waveforms

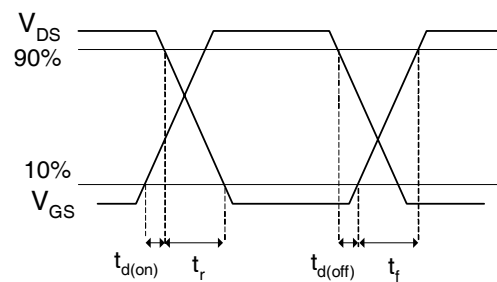


Fig 15b. Switching Time Waveforms

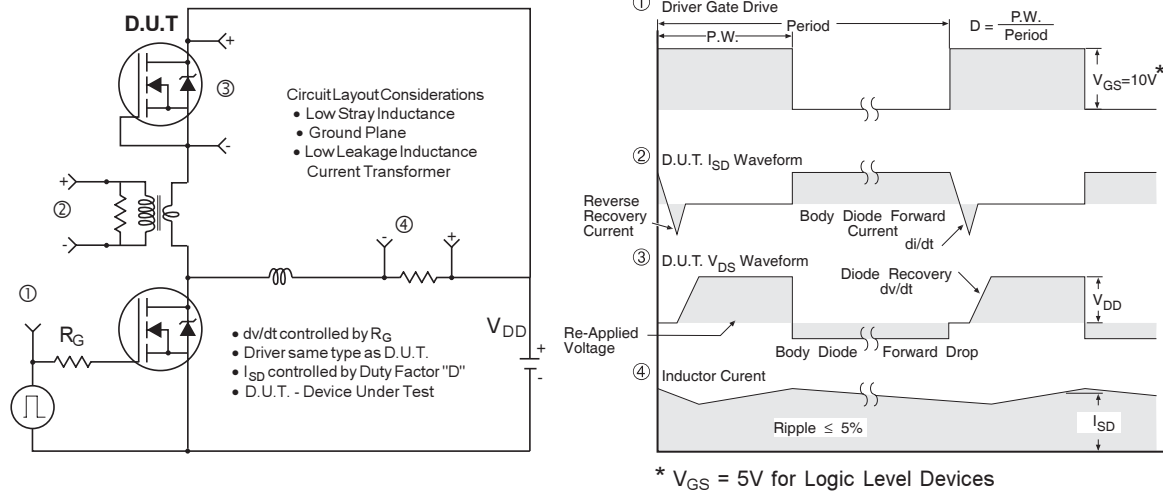


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

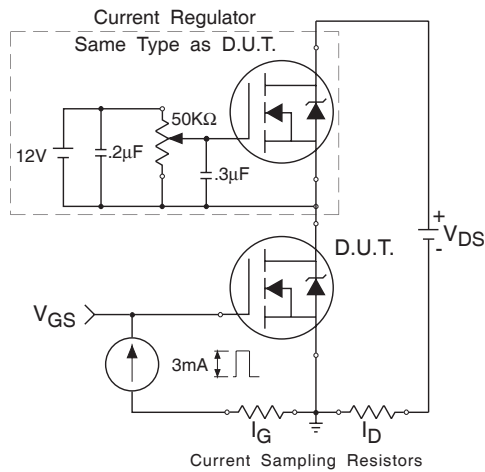


Fig 17. Gate Charge Test Circuit

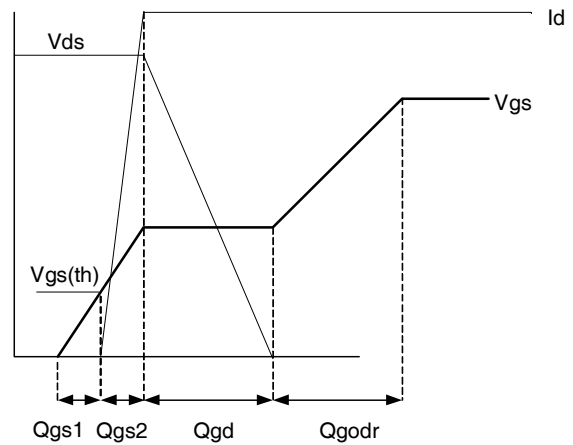
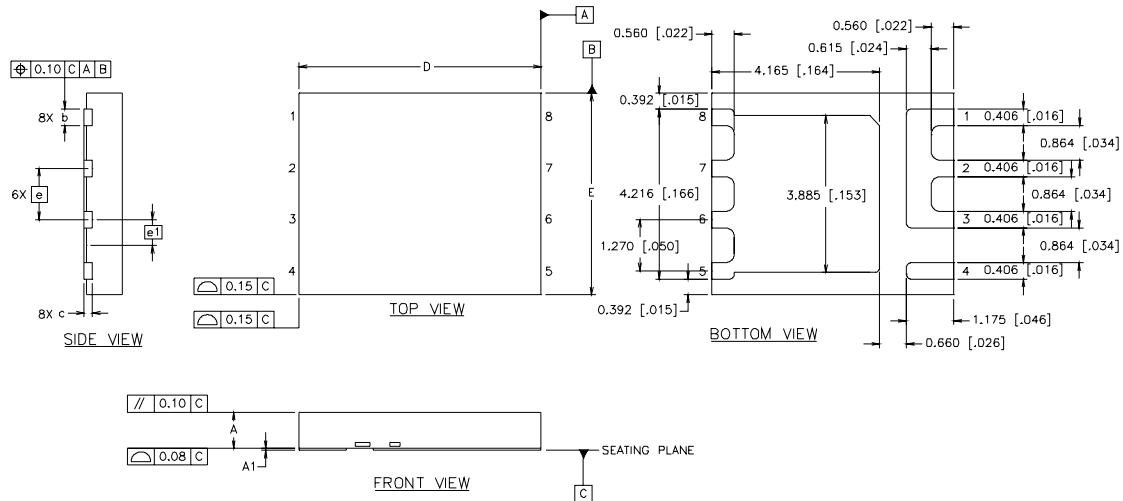


Fig 18. Gate Charge Waveform

IRFH5053PbF

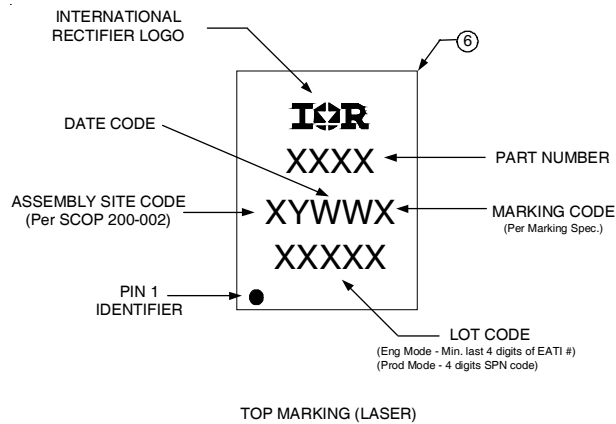
PQFN Package Details

International
IR Rectifier



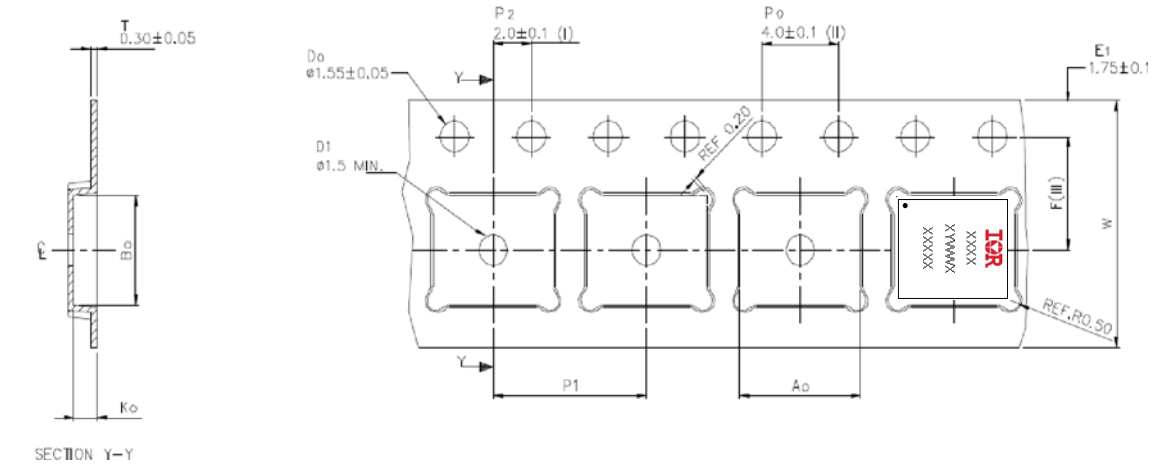
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0315	.0394	0.800	1.000
A1	.0000	.0020	0.000	0.050
b	.0140	.0180	0.356	0.456
c	.0080 REF.		0.203 REF.	
D	.2362 BASIC		6.0 BASIC	
E	.1969 BASIC		5.0 BASIC	
e	.0500 BASIC		1.270 BASIC	
e1	.0250 BASIC		0.635 BASIC	

PQFN Part Marking



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

PQFN Tape and Reel



A0	6.30 +/− 0.1
B0	5.30 +/− 0.1
K0	1.20 +/− 0.1
F	5.50 +/− 0.1
P1	8.00 +/− 0.1
W	12.00 +/− 0.3

- (I) Measured from centreline of sprocket hole to centreline of pocket.
- (II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .
- (III) Measured from centreline of sprocket hole to centreline of pocket.
- (IV) Other material available.
- (V) Typical SR of form tape Max 10^{-9} OHM/SQ

ALL DIMENSIONS IN MILLIMETRES UNLESS OTHERWISE STATED

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.75\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 7.4\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_{thjc} is guaranteed by design
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.12/08

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenhheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Infineon:](#)

[IRFH5053TRPBF](#) [IRFH5053TRPBFXUMA1](#)